

AOI478-VB Datasheet N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
100	0.110 at V _{GS} = 10 V	15		
	0.115 at V _{GS} = 6 V	15		

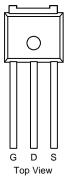
FEATURES

- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g Tested

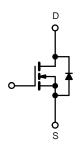
APPLICATIONS

• Primary Side Switch





TO-251



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C =	25 °C, unless othe	rwise noted)		
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	± 20	V	
	T _C = 25 °C		15	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	I _D	8.7	
Pulsed Drain Current		I _{DM}	45	А
Continuous Source Current (Diode Conduction)	۱ _S	15		
Avalanche Current	I _{AR}	15	1	
Repetitive Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AR}	11.3	mJ
	T _C = 25 °C	P _D	61 ^b	w
Maximum Power Dissipation	T _A = 25 °C		2.7 ^a	vv
Operating Junction and Storage Temperature Range	·	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
hunding to Ambiguid	t ≤ 10 s	R _{thJA}	16	20	°C/W	
Junction-to-Ambient ^a	Steady State		45	55		
Junction-to-Case	•	R _{thJC}	2	2.4		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static		· · · · · ·					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	100			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0		3.0 V	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		V _{DS} = 100 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 \text{ °C}$			50	μA	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	15			А	
		V _{GS} = 10 V, I _D = 15 A		0.110		Ω	
	Б	V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C		0.170			
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C		0.230			
		V _{GS} = 6 V, I _D = 10 A		0.115			
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		25		S	
Dynamic ^a							
Input Capacitance	C _{iss}			892		pF	
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		110			
Reverse Transfer Capacitance	C _{rss}			70			
Total Gate Charge ^c	Qg			20	25		
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 75 V, V_{GS} = 10 V, I_{D} = 15 A		5.5		nC	
Gate-Drain Charge ^c	Q _{gd}			7			
Gate Resistance	R _g		1		3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			8	12		
Rise Time ^c	t _r	V_{DD} = 75 V, R_L = 5 Ω		35	55	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ 15 A, V_{GEN} = 10 V, R_G = 2.5 Ω		17	25		
Fall Time ^c	t _f]		30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	_C = 25 °C)		·			
Pulsed Current	I _{SM}				45	А	
Diode Forward Voltage ^b	V _{SD}	I _F = 15 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 15 A, dl/dt = 100 A/μs		55	85	ns	

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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55 °C

6

5

 $V_{GS} = 10 V$

20

25

T_C = 125 °C

25 °C

3

4

2

10

16

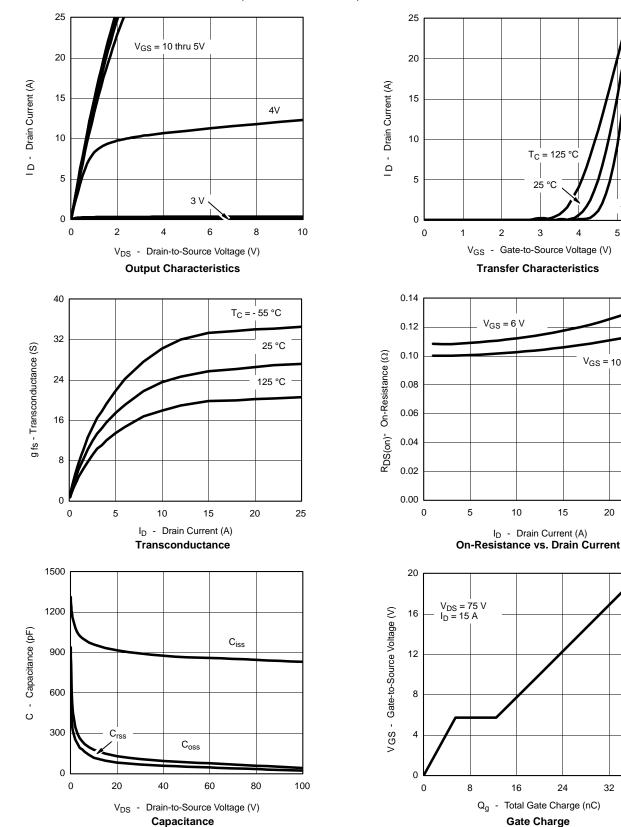
Gate Charge

24

32

40

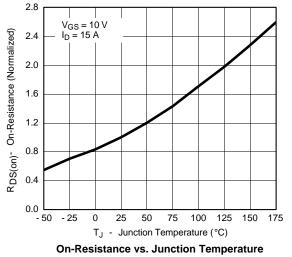
15



TYPICAL CHARACTERISTICS (25 °C unless noted)



TYPICAL CHARACTERISTICS (25 °C unless noted)



THERMAL RATINGS

2

1

0.1

0.01

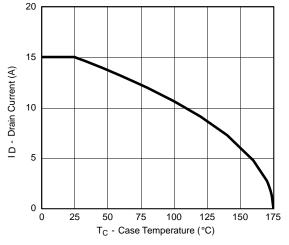
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Normalized Effective Transient Thermal Impedance Duty Cycle = 0.5

0.02

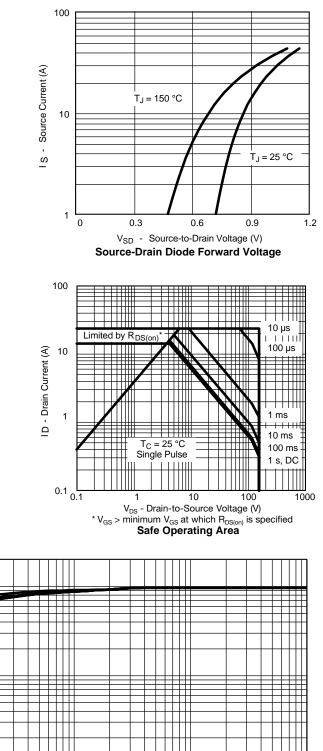
D.05 Single Pulse

0.2 0.1

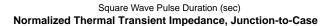


Maximum Avalanche Drain Current vs. Case Temperature

10⁻³



1



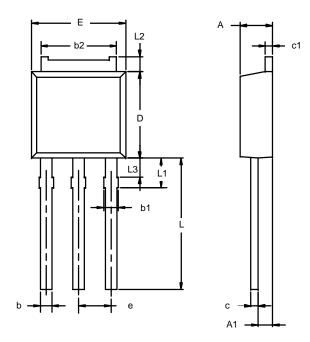
10⁻¹

10-2

10



TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

	MILLIN	IETERS	INCHES		
Dim	Min	Max	Min	Max	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
b	0.71	0.89	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.43	0.206	0.214	
С	0.46	0.58	0.018	0.023	
c1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
Е	6.48	6.73	0.255	0.265	
е	2.28	BSC	0.090) BSC	
L	8.89	9.53	0.350	0.375	
L1	1.91	2.28	0.075	0.090	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.045	0.060	



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